



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION # 16790AB

Generic Copy

Issue Date: 13-Apr-2012

TITLE: Final PCN for transfer wafer fab from Gunma to Niigata in Japan.(Group B)

PROPOSED FIRST SHIP DATE: starting 31 July 2012 until 30 June 2013 (the actual ship date will be different by each product, please check the responsible Sales person).

AFFECTED CHANGE CATEGORY(S): Wafer Fabrication Location Change

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Tetsuya.Ishizuka@onsemi.com

SAMPLES: Contact your local ON Semiconductor Sales Office or Akira.Yoneyama@onsemi.com

ADDITIONAL RELIABILITY DATA: May be available

Contact your local ON Semiconductor Sales Office or Shoji.Suematsu@onsemi.com.

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>

DESCRIPTION AND PURPOSE:

This is a Final Process Change Notification to announce the transfer of products from Sanyo wafer fabrication sites located in Gunma to Niigata.

The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.



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RELIABILITY DATA SUMMARY

Group B

| Test: | Conditions: | Interval: | Results |
|------------------------------|---------------------------------|-----------|---------|
| High Temp Operating Life | Tj=Tjmax, Vcc(Vdd)opemax | 1000 hrs | 0/77 |
| Temp Humidity Bias * | Ta=85C, RH=85%, VCC=recommended | 1000 hrs | 0/77 |
| Temp Humidity Storage * | Ta=85C RH=85% | 1000 hrs | 0/77 |
| Temp Cycle * | Ta=-55C to 150C | 100 cyc | 0/77 |
| High Temp Storage | Ta=150C | 1000 hrs | 0/77 |
| Electrostatic Discharge (MM) | C=200pF, R=0Ω | 150V | 0/3 |

Note) The test items with * make are put into operation after the preconditioning
 (surface-mount device : Reflow Soldering, through-hole device :Flow Soldering)
 Temp Humidity Bias Test: Power Dissipation >= 0.1W.
 Intermittent power application consists of 1-hour ON and 3-hours OFF.

ELECTRICAL CHARACTERISTIC SUMMARY

No change to the device data sheets is being made. All parametric performance and limits remain the same.

CHANGED PART IDENTIFICATION

No change to current part marking will occur. Marking traceability codes will be able to identify wafer fab die source.

List of affected Generic parts:

Group B

| PART_ID |
|---------------|
| LA4631-E |
| LB1862M-TLM-E |
| LB1962M-MPB-E |
| LB1962M-TLM-E |